2.5V Drive Nch MOS FET RTR025N03

●Structure

Silicon N-channel MOS FET

● Features

- 1) Low On-resistance.
- 2) Space saving-small surface mount package (TSMT3).
- 3) Low voltage drive (2.5V drive).

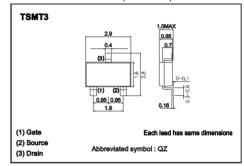
Applications

Switching

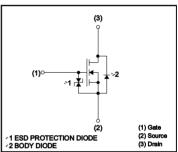
●Packaging specifications and hFE

	Package	Taping		
Туре	Code	TL		
	Basic ordering unit (pieces)	3000		
RTR025	0			

■External dimensions (Unit : mm)



●Inner circuit



● Absolute maximum ratings (Ta=25 °C)

Parameter Drain-source voltage Gate-source voltage		Limits	Unit	
		30	V	
		12	V	
Continuous	lο	±2.5	Α	
Pulsed	IDP ·1	±10	Α	
Continuous	ls	0.8	Α	
Pulsed	Isp ·1	10	Α	
Total power dissipation		1.0	W	
Channel temperature		150	°C	
Range of storage temperature		-55 to +150	°C	
	Pulsed Continuous Pulsed	Pulsed IDP ·1 Continuous Is Pulsed IsP ·1 Po ·2 Tch	Voss 30 Voss 12 Continuous ID ±2.5 Pulsed IDP · 1 ±10 Continuous Is 0.8 Pulsed IsP · 1 10 PD · 2 1.0 Tch 150	

v1 Pw 10μs, Duty cycle 1% v2 Mounted on a ceramic board

●Thermal resistance

Parameter	Symbol	Limits	Unit	
Channel to ambient	Rth(ch-a)*	125	∘C/W	

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	lgss	-	_	10	μA	V _{GS} =12V, V _{DS} =0V
Drain-source breakdown voltage	V _{(BR) DSS}	30	_	-	٧	I _D = 1mA, V _{GS} =0V
Zero gate voltage drain current	IDSS	_	_	1	μA	V _{DS} = 30V, V _{GS} =0V
Gate threshold voltage	VGS (th)	0.5	_	1.5	٧	V _{DS} = 10V, I _D = 1mA
Otatia daria arrana arratata	RDS (on)	-	66	92	mΩ	I _D = 2.5A, V _{GS} = 4.5V
Static drain-source on-state resistance		_	70	98	mΩ2	I _D = 2.5A, V _{GS} = 4V
resistance		_	95	133	mΩ2	I _D = 2.5A, V _{GS} = 2.5V
Forward transfer admittance	Y _{fs}	2.0	_	_	S	V _{DS} = 10V, I _D = 2.5A
Input capacitance	Ciss	_	220	_	pF	V _{DS} = 10V
Output capacitance	Coss	_	60	_	pF	V _{GS} =0V
Reverse transfer capacitance	Crss	_	35	_	рF	f=1MHz
Turn-on delay time	td (on)	-	9	_	ns	VDD= 15V
Rise time	t	_	15	_	ns	ID= 1.25A
Turn-off delay time	td (off) "	_	25	_	ns	Vgs= 4.5V RL=12Ω
Fall time	tr	_	10	_	ns	Rg=10Ω
Total gate charge	Qg	-	3.3	4.6	nC	V _{DD} =15V V _{GS} =4.5V
Gate-source charge	Qgs	_	0.7	_	nC	I _D = 2.5A
Gate-drain charge	Qgd	_	1.0	_	nC	RL=6Ω Rg=10Ω

Pulsed

●Body diode characteristics (Source-drain) (Ta=25^{tt}C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsp	_	_	1.2	V	Is= 0.8A, V _{GS} =0V

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